

2N2326A

SILICON CONTROLLED RECTIFIER
1.6 AMP, 400 VOLT



TO-39 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2326A is a hermetically sealed silicon controlled rectifier designed for sensing circuit applications and control systems.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Forward Voltage	V_{DRM}	200	V
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	300	V
RMS On-State Current	$I_{\text{T(RMS)}}$	1.6	A
Average On-State Current ($T_C=85^{\circ}\text{C}$)	$I_{\text{T(AV)}}$	1.0	A
Peak One Cycle Surge Current ($t=8.3\text{ms}$)	I_{TSM}	15	A
Peak Gate Power Dissipation	P_{GM}	100	mW
Average Gate Power Dissipation	$P_{\text{G(AV)}}$	10	mW
Peak Gate Current	I_{GM}	100	mA
Peak Gate Voltage	V_{GM}	6.0	V
Operating Junction Temperature	T_{J}	-65 to +125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{DRM}	$V_{\text{DRM}}=200\text{V}$, $R_{\text{GK}}=2.0\text{K}\Omega$		5.0	μA
I_{RRM}	$V_{\text{RRM}}=200\text{V}$, $R_{\text{GK}}=2.0\text{K}\Omega$		5.0	μA
I_{GT}	$V_{\text{D}}=6.0\text{V}$, $R_{\text{L}}=100\Omega$		20	μA
I_{H}	$V_{\text{D}}=6.0\text{V}$, $R_{\text{GK}}=2.0\text{K}\Omega$		2.0	mA
V_{GT}	$V_{\text{D}}=6.0\text{V}$, $R_{\text{L}}=100\Omega$		0.6	V
V_{TM}	$I_{\text{T}}=1.0\text{A}$, $t_{\text{p}}=380\mu\text{s}$		1.5	V

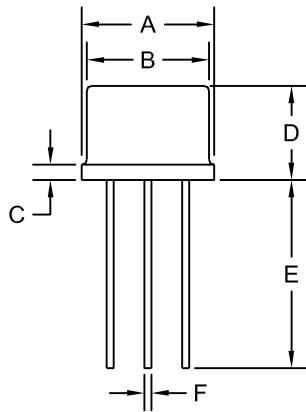
R0 (29-June 2016)

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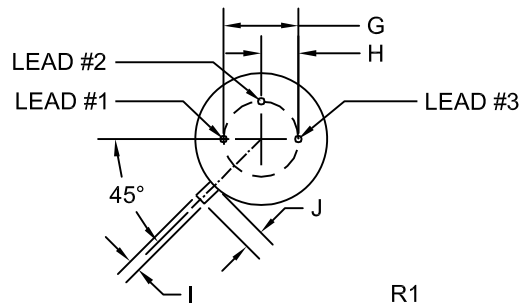


TO-39 CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)



LEAD CODE:

- 1) Cathode
- 2) Gate
- 3) Anode (case)

MARKING: FULL PART NUMBER

R0 (29-June 2016)

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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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